

Fig.1.

Growth of multiple non-compositional-graded layers

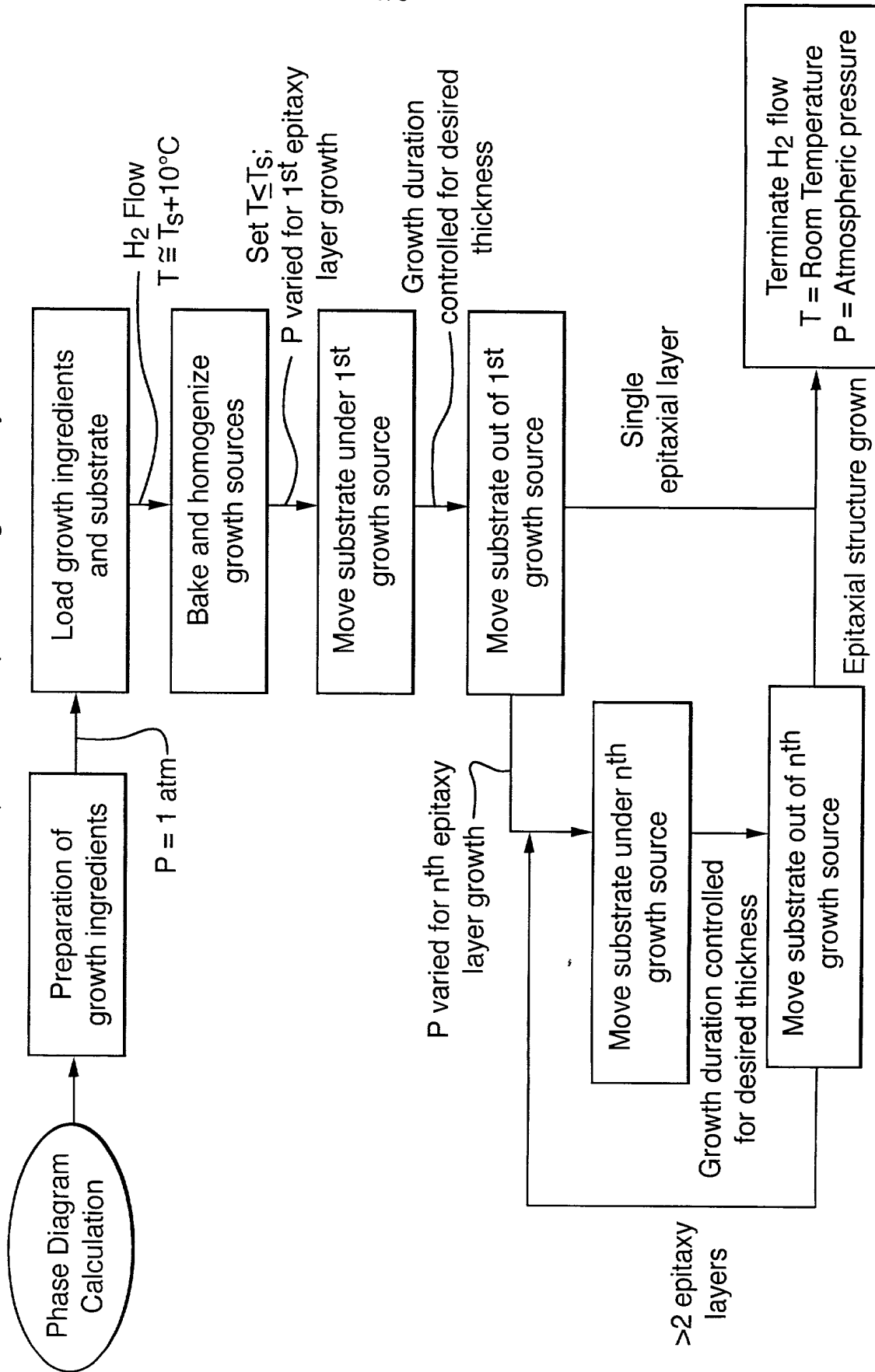


Fig.2.

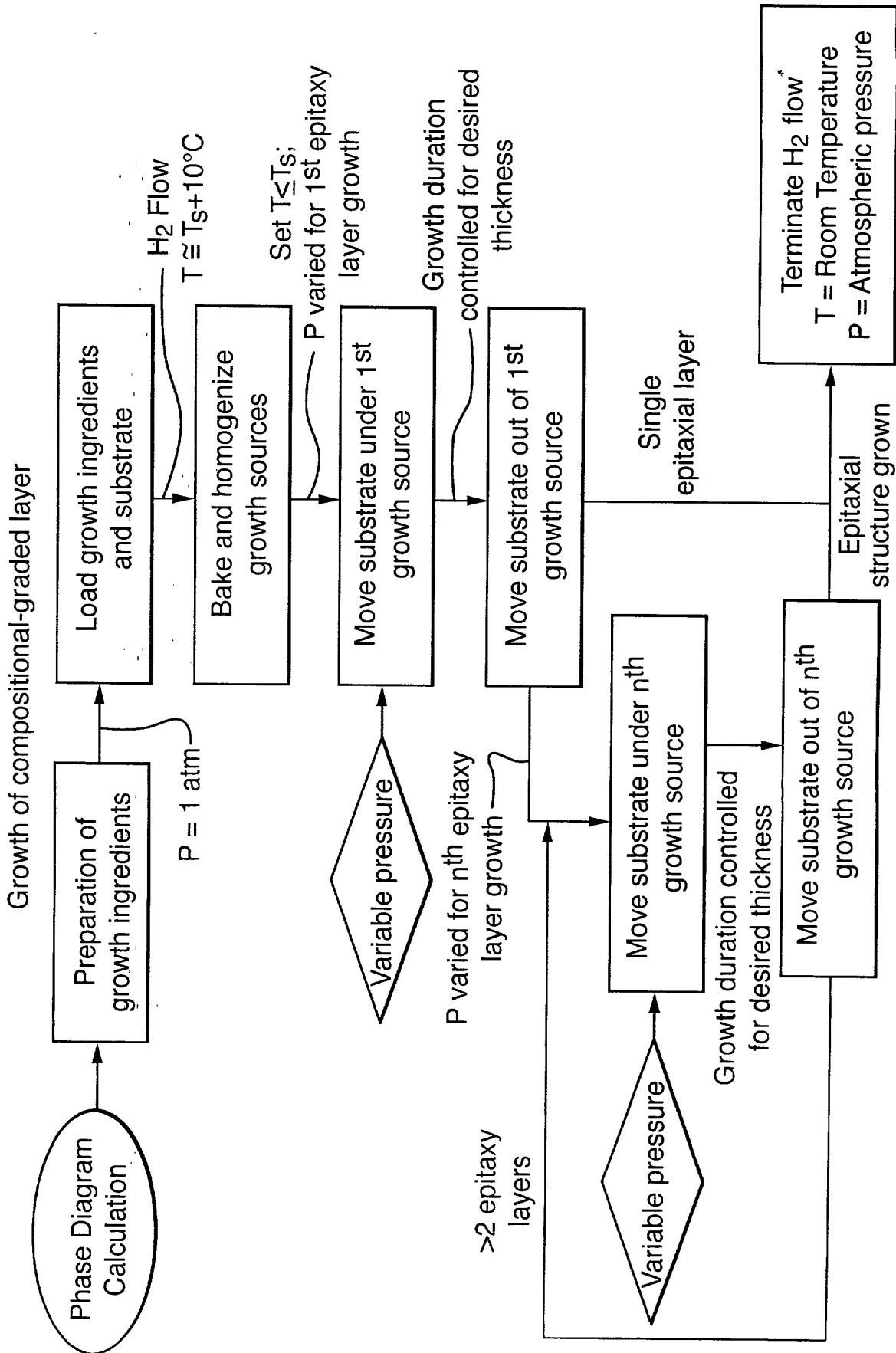


Fig.3.

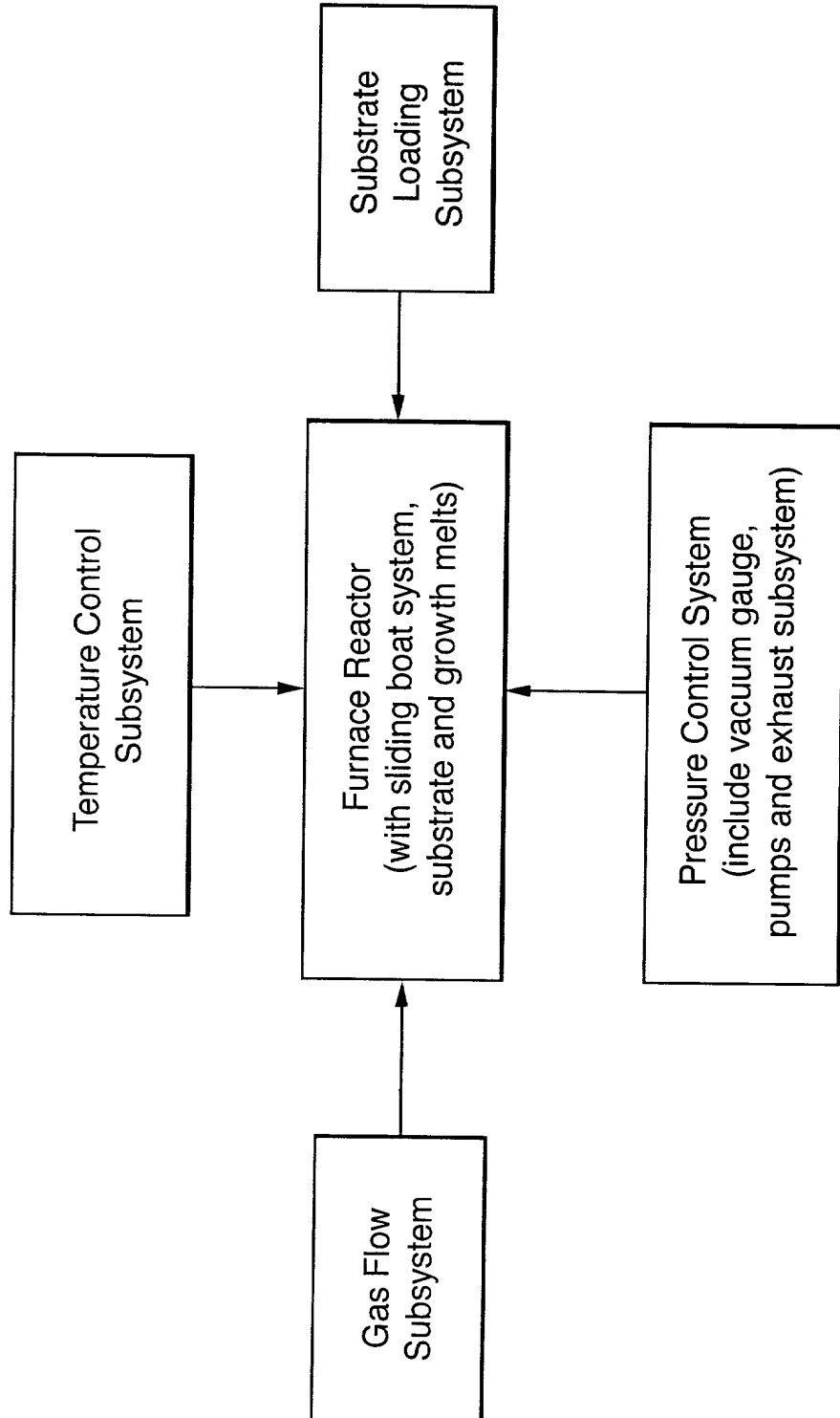
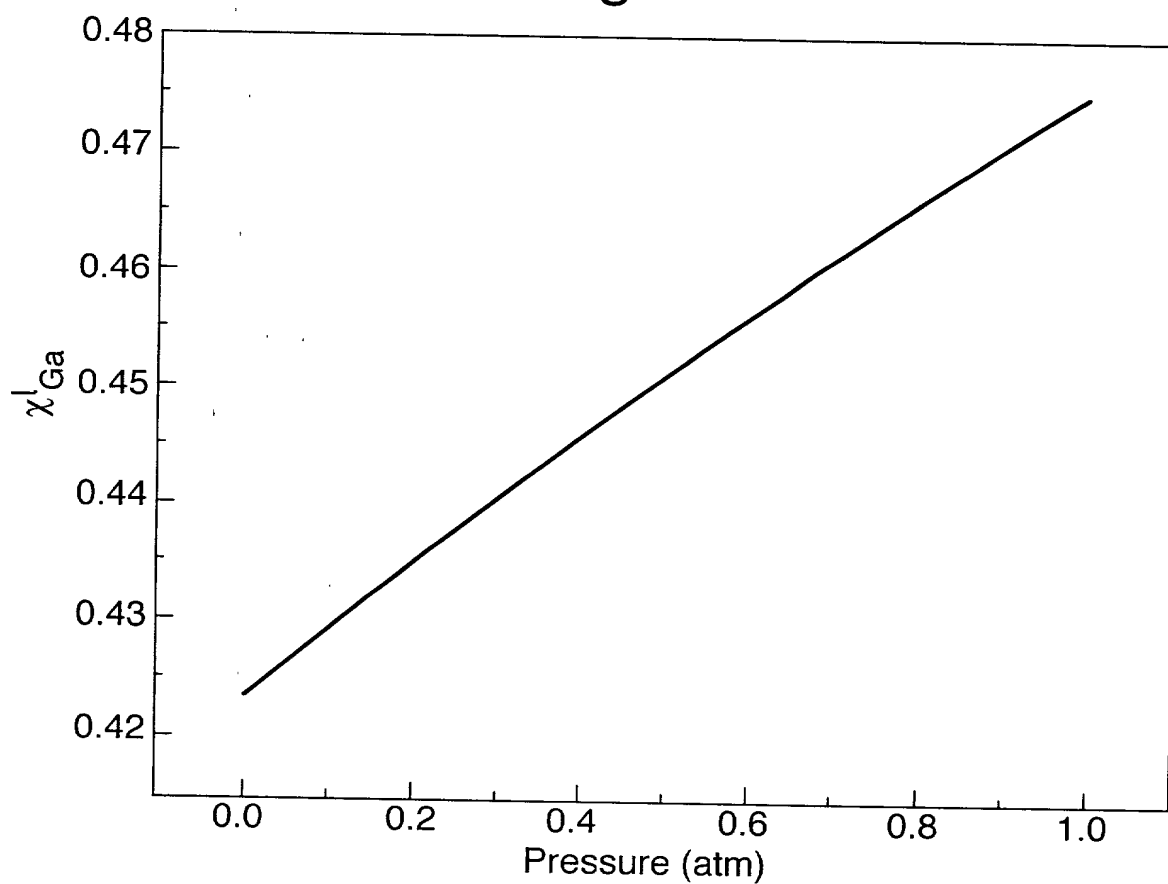
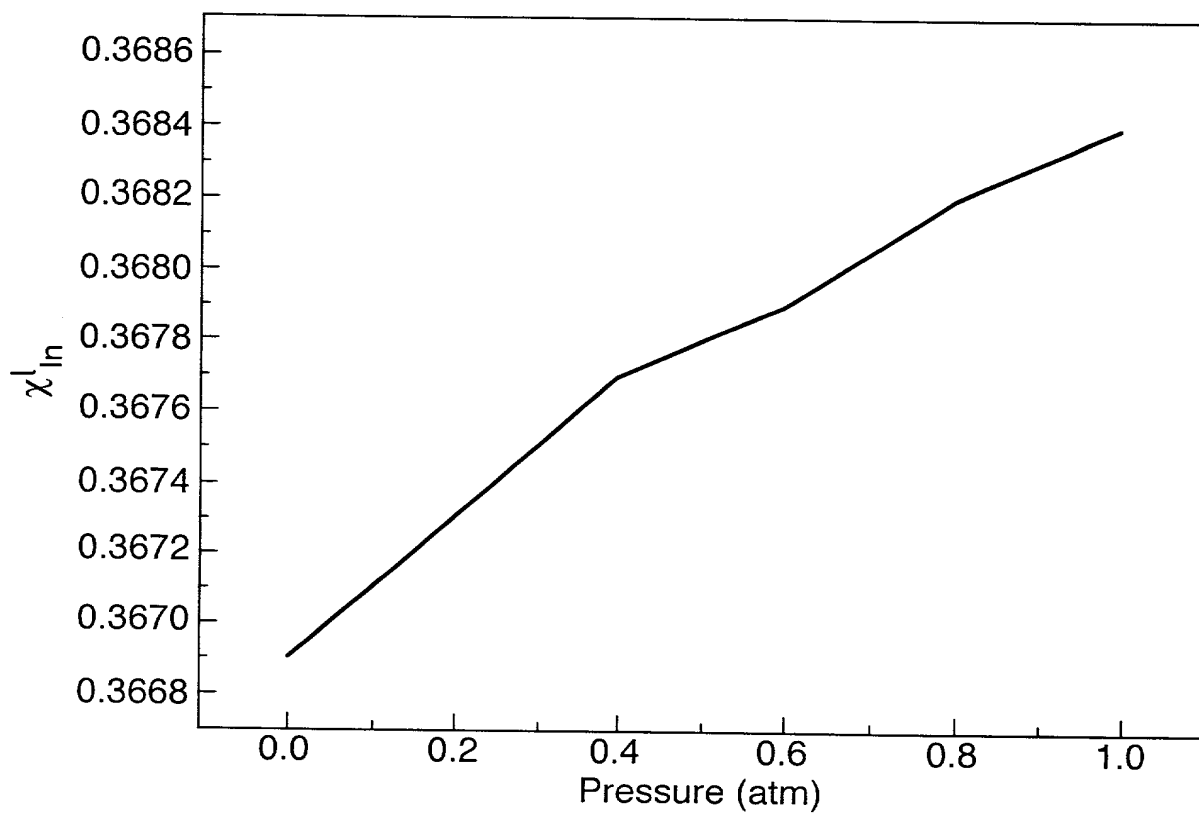


Fig.4.



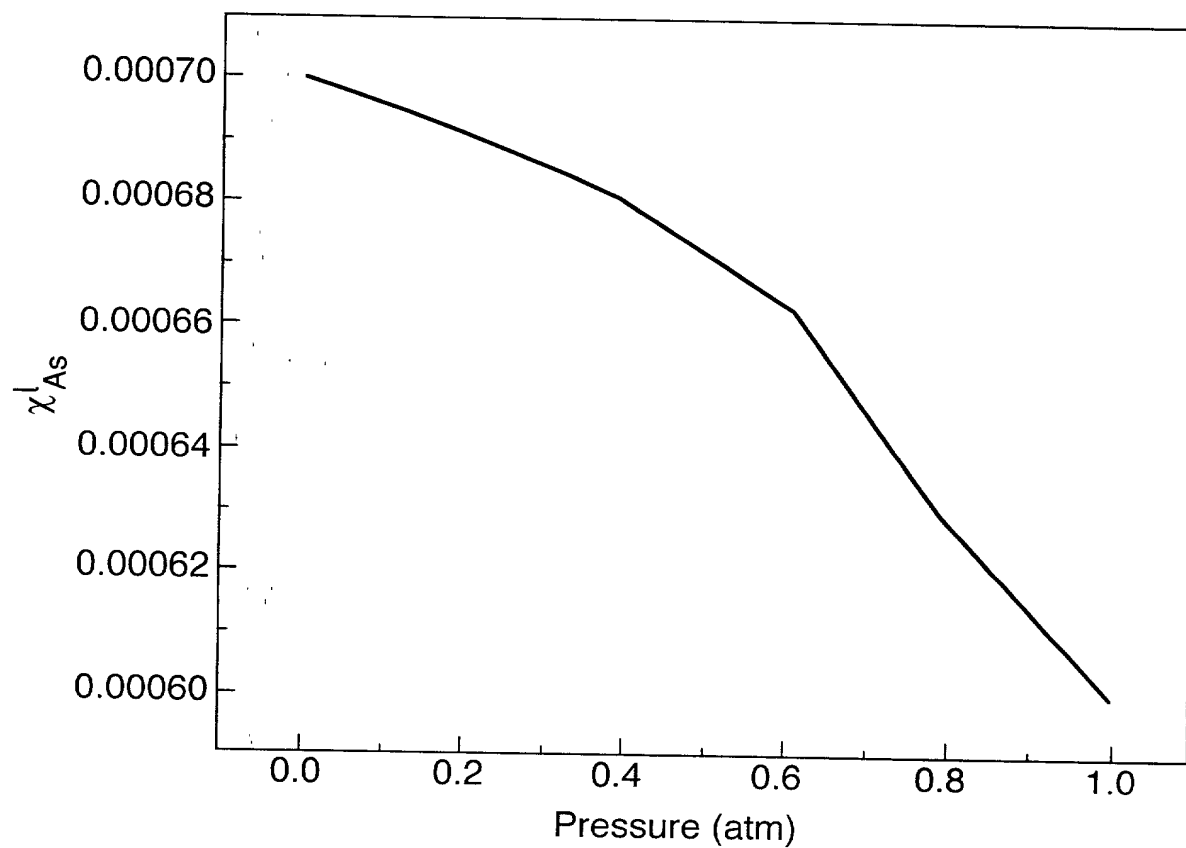
Atomic fraction  $\chi_{\text{Ga}}^l$  in melt for  $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$  growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.5.



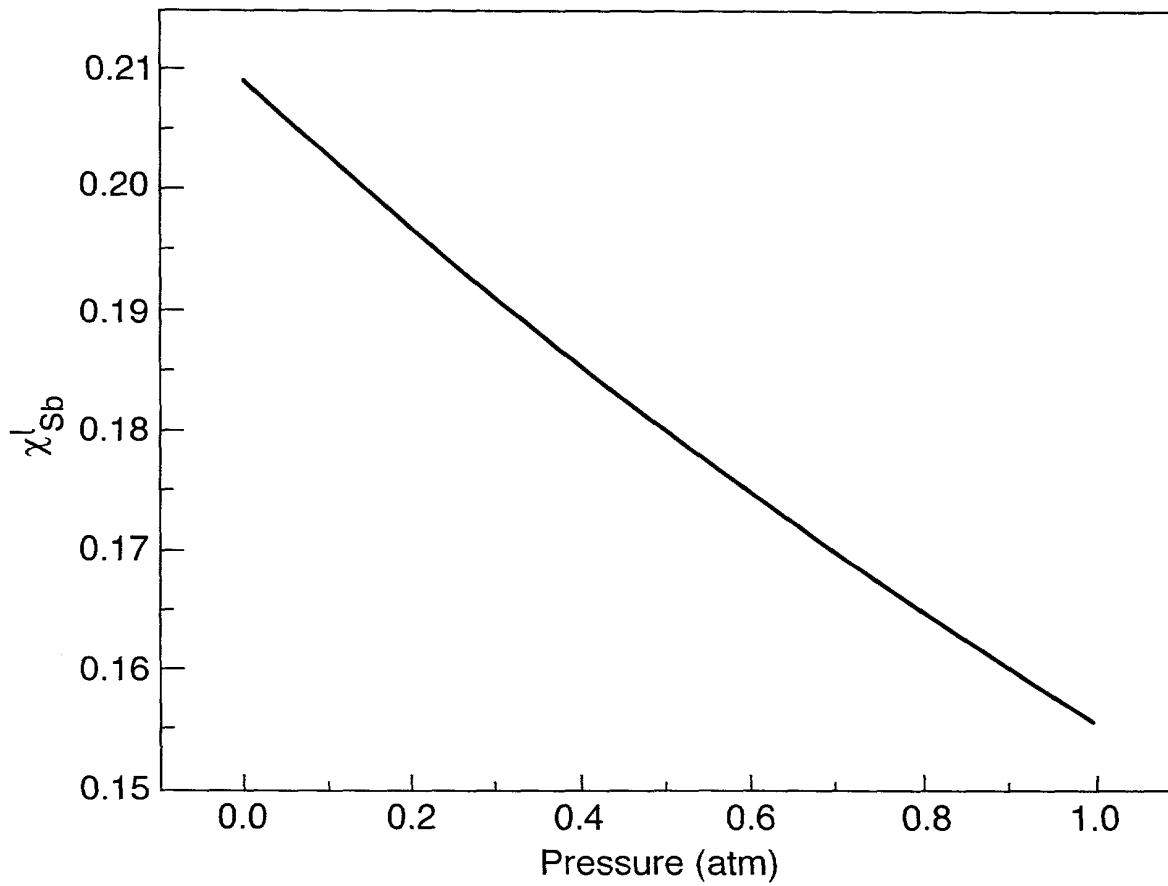
Atomic fraction  $\chi_{\text{In}}^l$  in melt for  $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$  growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.6.



Atomic fraction  $\chi_{As}^l$  in melt for  $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$  growth on GaSb (100) substrate at  $550^\circ\text{C}$  as a function of pressure.

Fig.7.



Atomic fraction  $\chi_{\text{Sb}}^l$  in melt for  $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$  growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.8(a).

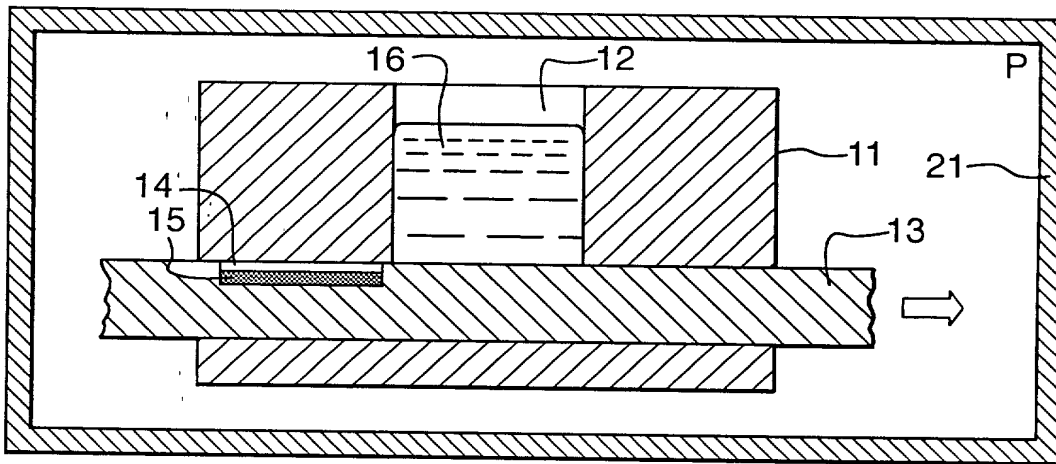


Fig.8(b).

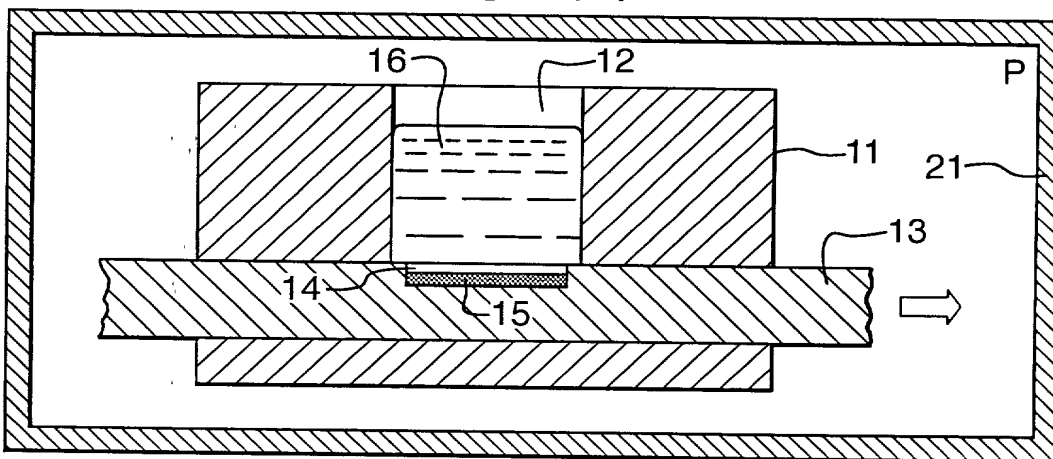


Fig.8(c).

